



### FEATURES

- Circular Active Area
- Ideal for Electron Detection
- High Speed
- Protective Cover Plate<sup>3</sup>

### Electro-Optical Characteristics at 25°C

Parameters	Test Conditions	Min	Typ	Max	Units
Active Area	9 mm		63		mm <sup>2</sup>
Responsivity	(see graphs on next page)				A/W
Reverse Breakdown Voltage, $V_R$	$I_R = 1 \mu A$	160			Volts
Capacitance, C	$V_R = 0 V$		700	2000	pF
Rise Time	$R_L = 50 \Omega, V_R = 150 V$			10	nsec
Dark Current	$V_R = 150 V$			100	nA

### Thermal Parameters

Storage and Operating Temperature Range	Units
Ambient <sup>1</sup>	-10°C to 40°C
Nitrogen or Vacuum	-20°C to 80°C
Lead Soldering Temperature <sup>2</sup>	260°C

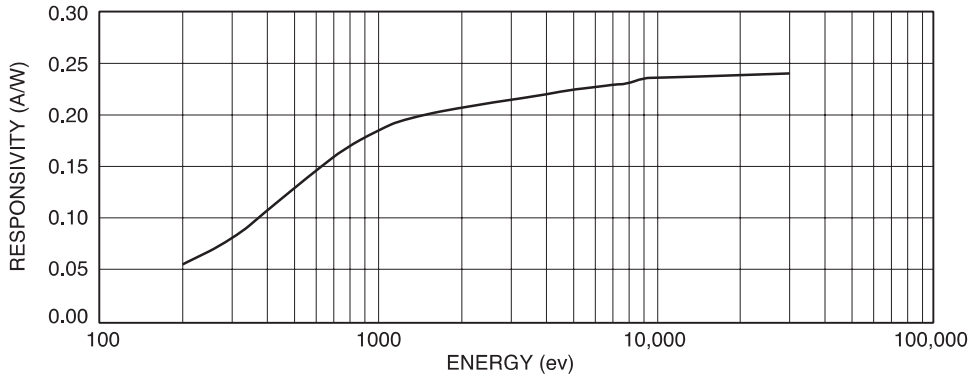
<sup>1</sup> Temperatures exceeding these parameters may create oxide growth on the active area. Over time responsivity to low energy radiation and wavelengths below 150 nm will be compromised.

<sup>2</sup> 0.080" from case for 10 seconds.

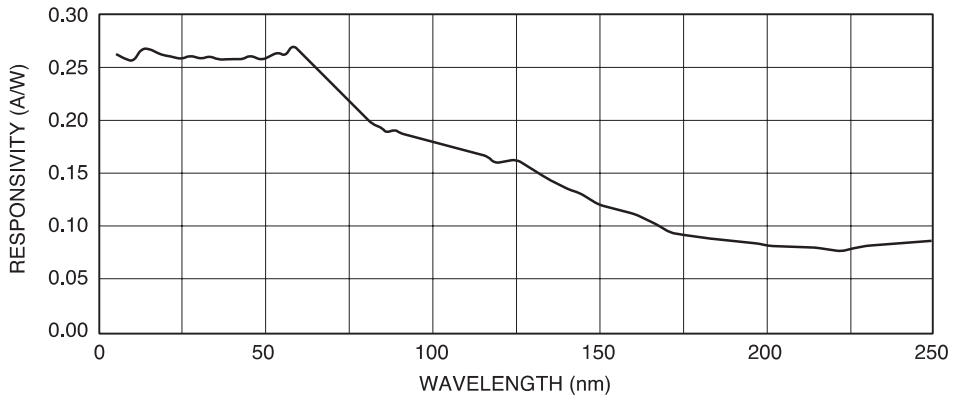
<sup>3</sup> Shipped with temporary cover to protect the photodiode array and wire bonds. Review the Application Note, "Handling Precautions for AXUV, SXUV, and UVG Detectors", prior to removing cover.



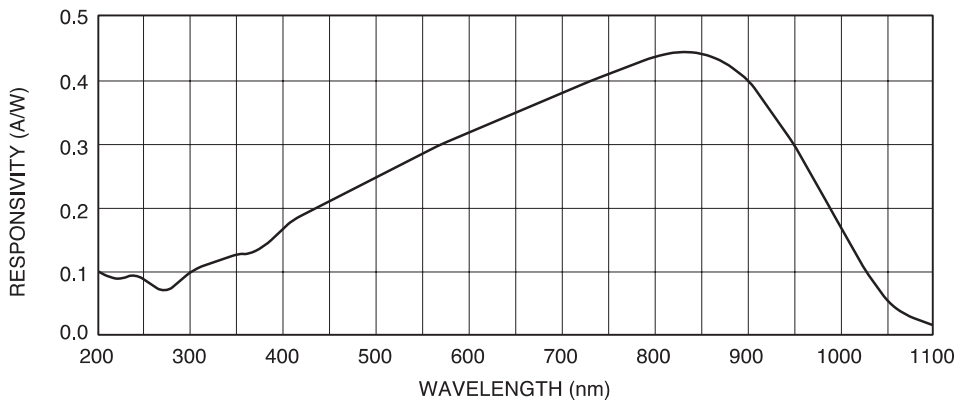
### Typical Electron Response



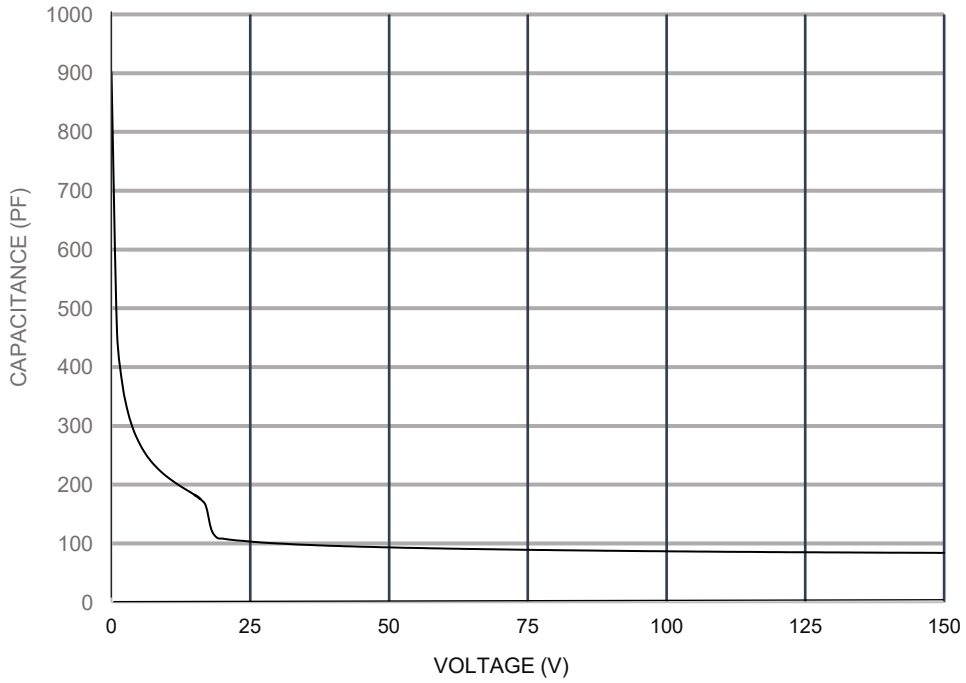
### Typical EUV-UV Photon Response



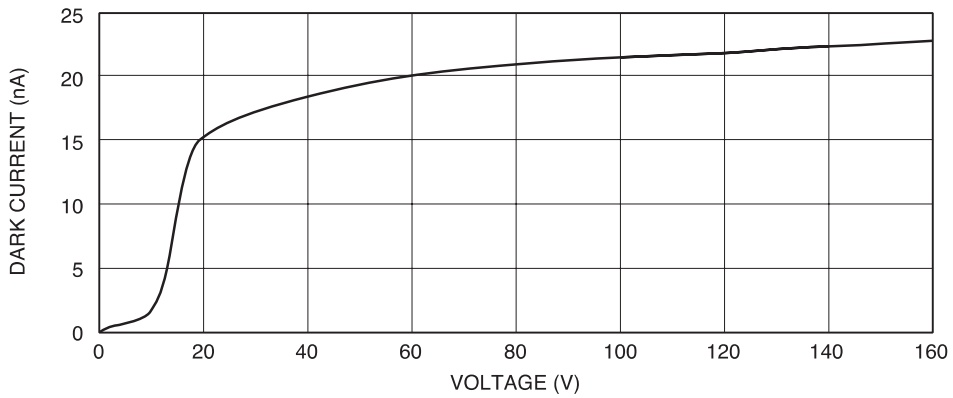
### Typical UV-VIS-NIR Photon Responsivity



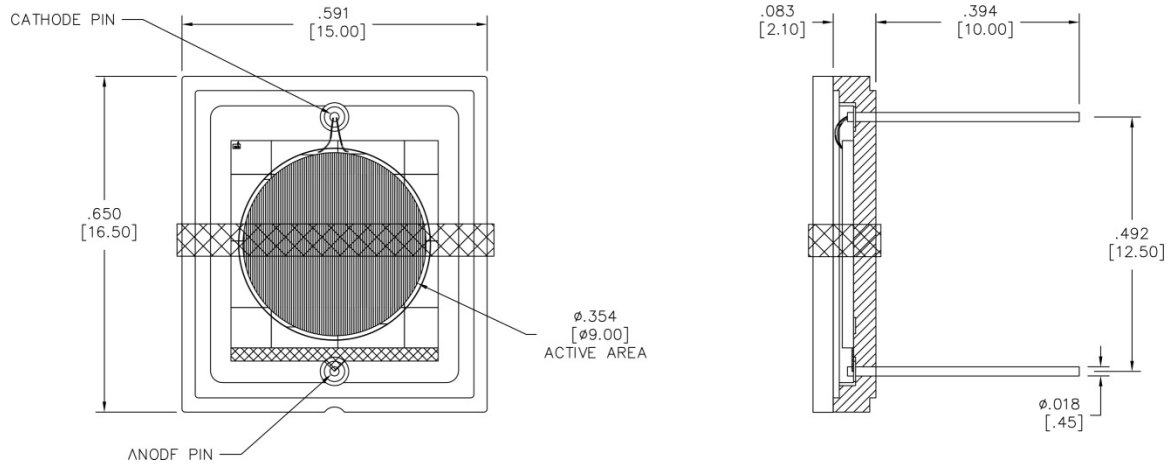
Capacitance vs. Voltage



Dark Current vs. Voltage



Package Information



Dimensions are in inch [metric] units.

Specifications are subject to change without prior notice.